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Jim  
(NW)  
**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re the Application of: INOUE, et al.

Group Art Unit: 2814

Serial No.: 09/473,988

Examiner: DOAN, Theresa T.

Filed: December 29, 1999

P.T.O. Confirmation No.: 1714

For. **SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME****PRELIMINARY AMENDMENT**Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Date: July 8, 2003

Sir:

Prior to continued examination, please amend the above-captioned patent application as follows:

**IN THE CLAIMS:****Please amend claims 1 and 8 as follows:**

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1. (Five Times Amended) A semiconductor device comprising an insulating interlayer formed on a conductive film, said insulating interlayer including:
- a first insulating layer of a composition containing SiH;
  - a second insulating layer formed on said first insulating layer; and
  - a third insulating layer formed between said conductive film and said first insulating layer, wherein said first insulating layer has an H content of not less than 15.4 atom% in the